Supporting information

Patterning of Amorphous-InGaZnO Thin-Film Transistors by Stamping of Surface-Modified Polydimethylsiloxane

Chungwan Gu and Jang-Sik Lee*

Department of Materials Science and Engineering, Pohang University of Science and Technology (POSTECH), Pohang 790-784, Republic of Korea

*E-mail: jangsik@postech.ac.kr

Fig. S1 Transferred IGZO layer on SiO$_2$/Si substrate. The PDMS stamp was not treated with piranha solution and UV-ozone.
Fig. S2 Optical absorbance of IGZO solution.

Fig. S3 Schematic illustration to show passivation of stamped layer by subsequent stamping process.
Fig. S4 The changes in electrical properties of stamped IGZO TFTs with the number of stamping layers.